TOSHIBA Transistor Silicon NPN Triple Diffused Type (Darlington power transistor)

2SD2526

High Power Switching Applications

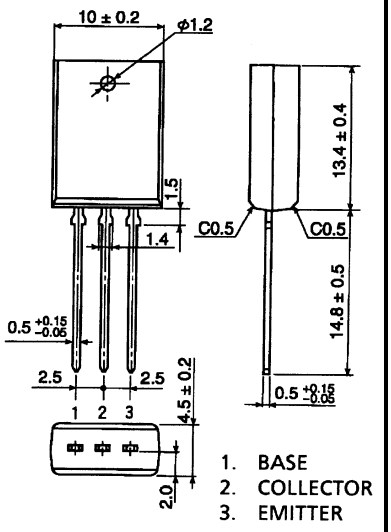
Hammer Drive, Pulse Motor Drive Applications

- High DC current gain: h_{FE} = 2000 (min) (V_{CE} = 3 V, I_C = 3 A)
- Low saturation voltage: $V_{CE\ (sat)}$ = 1.5 V (max) (I_C = 3 A)
- Complementary to 2SB1641

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	100	V
Collector-emitter voltage		V_{CEO}	100	V
Emitter-base voltage		V_{EBO}	7	V
Collector current	DC	I_C	5	A
	Pulse		8	
Base current		I_B	0.5	A
Collector power dissipation		P_C	1.8	W
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

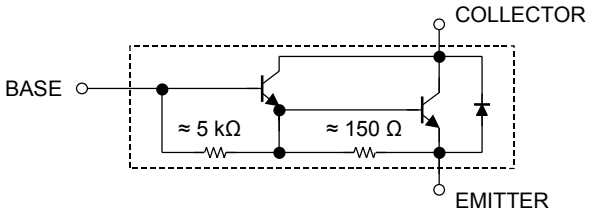
Unit: mm



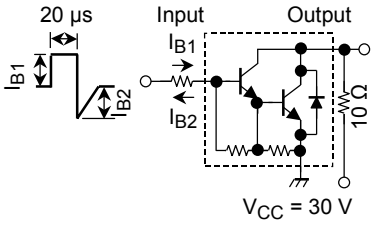
JEDEC	—
JEITA	—
TOSHIBA	2-10T1A

Weight: 1.5 g (typ.)

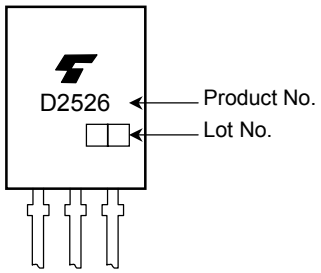
Equivalent Circuit



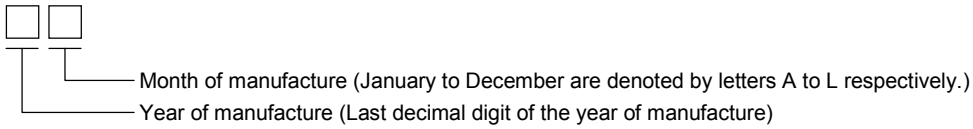
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I_{CBO}	V_{CB} = 100 V, I_E = 0	—	—	100	μA
Emitter cut-off current		I_{EBO}	V_{EB} = 6 V, I_C = 0	—	—	2.5	mA
Collector-emitter breakdown voltage		$V_{(BR)\ CEO}$	I_C = 30 mA, I_B = 0	100	—	—	V
DC current gain		$h_{FE\ (1)}$	V_{CE} = 3 V, I_C = 3 A	2000	—	15000	
		$h_{FE\ (2)}$	V_{CE} = 3 V, I_C = 5 A	1000	—	—	
Collector-emitter saturation voltage		$V_{CE\ (sat)\ (1)}$	I_C = 3 A, I_B = 6 mA	—	1.1	1.5	V
		$V_{CE\ (sat)\ (2)}$	I_C = 5 A, I_B = 20 mA	—	1.3	2.5	
Base-emitter saturation voltage		$V_{BE\ (sat)}$	I_C = 3 A, I_B = 6 mA	—	1.7	2.5	V
Switching time	Turn-on time	t_{on}	 $I_{B1} = -I_{B2}$ = 6 mA, duty cycle ≤ 1%	—	1.0	—	μs
	Storage time	t_{stg}		—	4.0	—	
	Fall time	t_f		—	2.5	—	

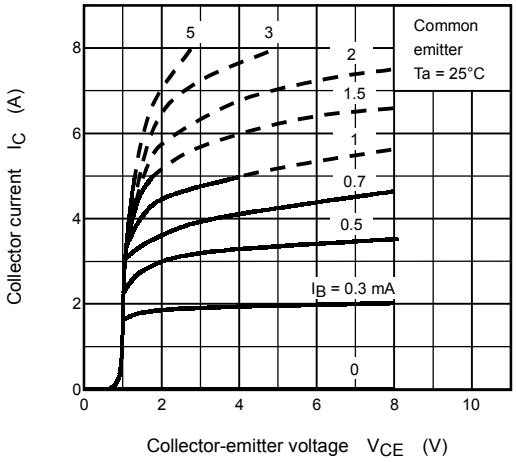
Marking



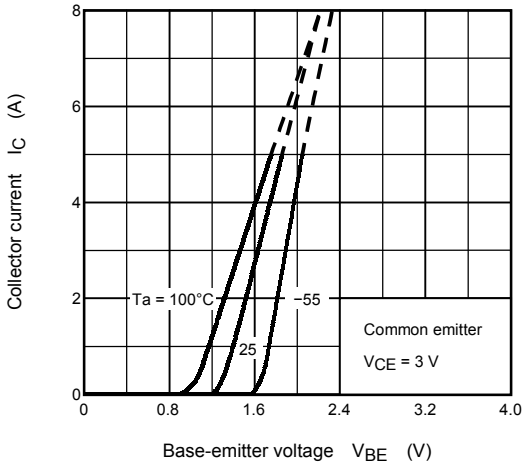
Explanation of Lot No.



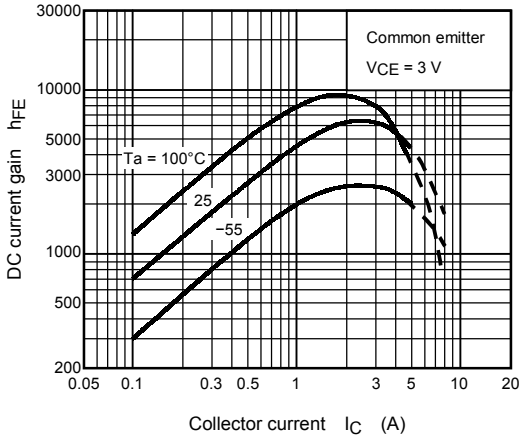
$I_C - V_{CE}$



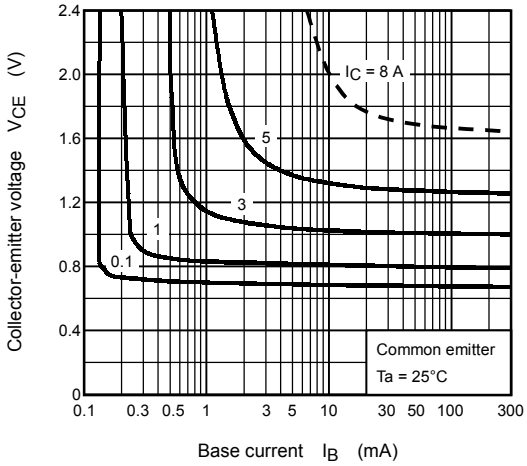
$I_C - V_{BE}$



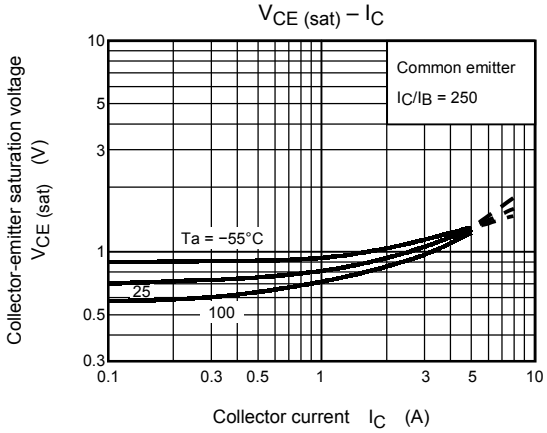
$h_{FE} - I_C$



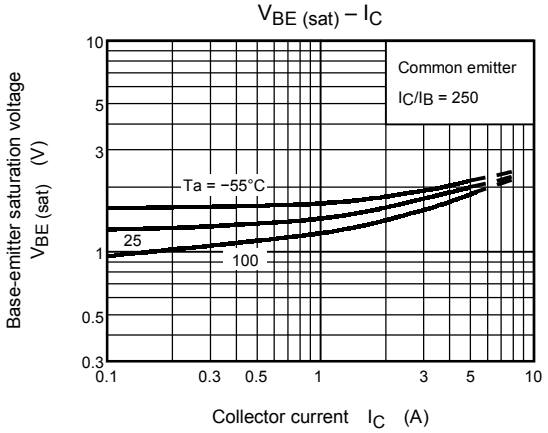
$V_{CE} - I_B$



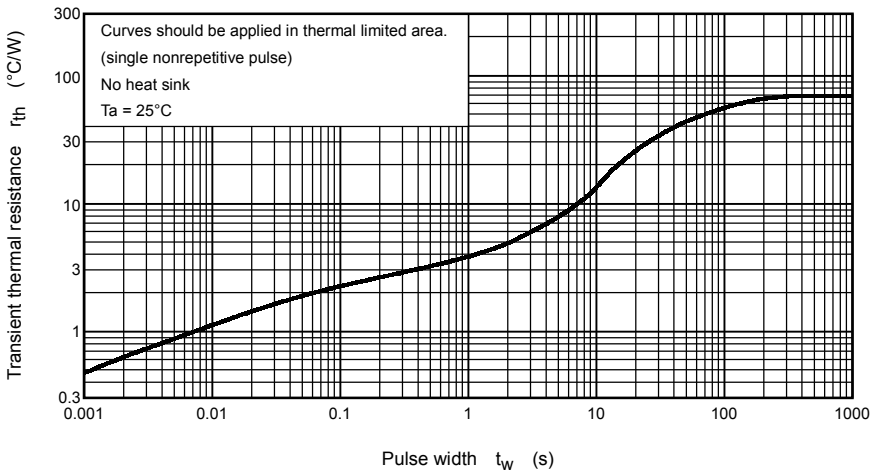
$V_{CE\ (sat)} - I_C$



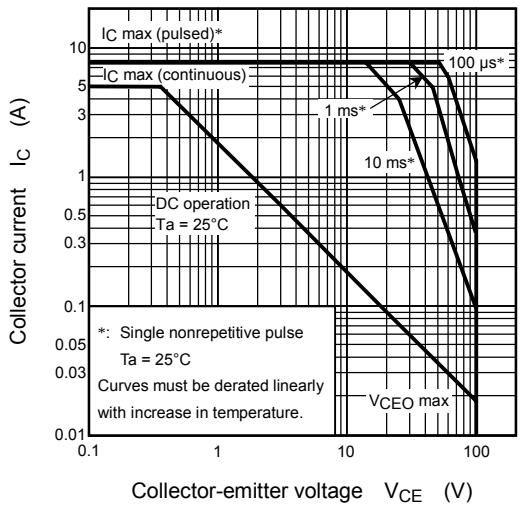
$V_{BE\ (sat)} - I_C$



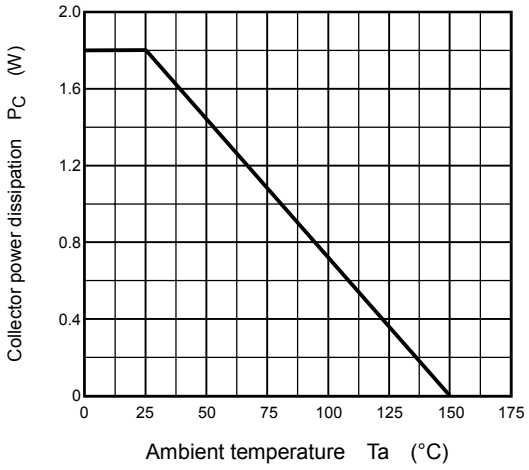
$r_{th} - t_w$



Safe Operating Area



$P_C - Ta$



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